

ABSTRACT OF THE DISCLOSURE

Disclosed is a technique capable of improving a yield of a semiconductor device by measuring a plurality of TEGs arranged in a scribe region. A first electrode pad connected 5 to each terminal of a TEG is formed as a rectangular, minute, isolated pattern having a side length of about $0.5 \mu\text{m}$ or shorter and constituted of an uppermost layer wiring on a semiconductor substrate, and therefore, a great number of TEGs can be laid in a first scribe region. The characteristic 10 evaluation or the failure analysis is performed by contacting a nanoprobe having a tip radius of curvature of $0.05 \mu\text{m}$ to $0.8 \mu\text{m}$ to the first electrode pad.